

# RC4558 Dual General-Purpose Operational Amplifier

#### 1 Features

- Wide common-mode and differential voltage
- No frequency compensation required
- Low power consumption
- No latch-up
- Gain bandwidth product: 4MHz typical
- Gain and phase match between amplifiers
- Low noise: 6.5nV/\(\sqrt{Hz}\) typical at 10kHz
- Low distortion and noise: 0.0001% at 1kHz

# 2 Applications

- **AV** receivers
- Professional audio mixers
- Soundbars
- Wireless speakers

## 3 Description

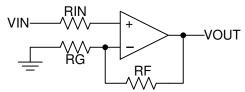
The RC4558 device is a dual general-purpose operational amplifier. The combination of the wide supply voltage range (10V to 30V), low noise (6.5nV/  $\sqrt{\text{Hz}}$ ), and distortion performance (0.0001% THD+N) of the device allow the RC4558 to be used in various audio applications.

The high common-mode input voltage range and the absence of latch-up of the device are designed for voltage-follower applications. The internal frequency compensation of the device allows for stability without external components.

#### Package Information (1)

| PART NUMBER | PACKAGE        | PACKAGE SIZE <sup>(2)</sup> |
|-------------|----------------|-----------------------------|
|             | D (SOIC, 8)    | 4.9mm × 6mm                 |
|             | DGK (VSSOP, 8) | 3mm × 4.9mm                 |
| RC4558      | P (PDIP, 8)    | 9.81mm × 9.43mm             |
|             | PW (TSSOP, 8)  | 3mm × 6.4mm                 |
|             | PS (SOP, 8)    | 6.2mm × 7.8mm               |

- For all available packages, see Section 10.
- The package size (length × width) is a nominal value and includes pins, where applicable.



**Noninverting Amplifier Schematic** 



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# **4 Pin Configuration and Functions**

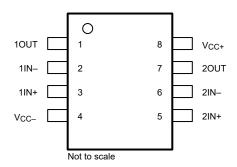


Figure 4-1. D, DGK, P, PS, or PW Package 8-Pin SOIC, VSSOP, PDIP, TSSOP or SOP (Top View)

**Table 4-1. Pin Functions** 

| PIN               |     | TYPE | DESCRIPTION        |  |  |  |
|-------------------|-----|------|--------------------|--|--|--|
| NAME              | NO. | ITPE | DESCRIPTION        |  |  |  |
| 1IN+              | 3   | I    | Noninverting input |  |  |  |
| 1IN-              | 2   | I    | Inverting Input    |  |  |  |
| 10UT              | 1   | 0    | Output             |  |  |  |
| 2IN+              | 5   | I    | Noninverting input |  |  |  |
| 2IN-              | 6   | I    | Inverting Input    |  |  |  |
| 2OUT              | 7   | 0    | Output             |  |  |  |
| V <sub>CC+</sub>  | 8   | _    | Positive Supply    |  |  |  |
| V <sub>CC</sub> - | 4   | _    | Negative Supply    |  |  |  |



## **5 Specifications**

## 5.1 Absolute Maximum Ratings

over operating ambient temperature range (unless otherwise noted)(1)

|                   |  | MIN | MAX  | UNIT |
|-------------------|--|-----|------|------|
| V <sub>CC+</sub>  | Supply voltage(2)                            |     | 18   | V    |
| V <sub>CC</sub> - | - Supply voltage <sup>(2)</sup>              |     | -18  | V    |
| V <sub>ID</sub>   | Differential input voltage <sup>(3)</sup>    |     | ±30  | V    |
| VI                | Input voltage (any input) <sup>(2) (4)</sup> |     | ±15  | V    |
| Io                | Output Current <sup>(5)</sup>                |     | ±125 | mA   |
| TJ                | Operating virtual junction temperature       |     | 150  | °C   |
| T <sub>STG</sub>  | Storage temperature                          | -65 | 150  | °C   |

- (1) Operation outside the Absolute Maximum Ratings may cause permanent device damage. Absolute Maximum Ratings do not imply functional operation of the device at these or any other conditions beyond those listed under Recommended Operating Conditions. If used outside the Recommended Operating Conditions but within the Absolute Maximum Ratings, the device may not be fully functional, and this may affect device reliability, functionality, performance, and shorten the device lifetime.
- (2) All voltage values, unless otherwise noted, are with respect to the midpoint between VCC+ and VCC-.
- (3) Differential voltages are at IN+ with respect to IN-.
- (4) The magnitude of the input voltage must never exceed the magnitude of the supply voltage or 15V, whichever is less
- (5) Temperature and supply voltages must be limited to ensure that the dissipation rating is not exceeded.

#### 5.2 ESD Ratings

|                               |                          |   | VALUE | UNIT |
|-------------------------------|--------------------------|---|-------|------|
| V                             | Electrostatic discharge  | Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 <sup>(1)</sup>     |       | V    |
| V <sub>(ESD)</sub> Electrosta | Liectrostatic discriarge | Charged-device model (CDM), per ANSI/ESDA/JEDEC JS-002 <sup>(2)</sup> | ±1500 | ]    |

- (1) JEDEC document JEP155 states that 500V HBM allows safe manufacturing with a standard ESD control process.
- 2) JEDEC document JEP157 states that 250V CDM allows safe manufacturing with a standard ESD control process.

#### 5.3 Recommended Operating Conditions

|                   |                                |         | MIN | MAX | UNIT |
|-------------------|--------------------------------|---------|-----|-----|------|
| V <sub>CC+</sub>  | Supply voltage                 |         | 5   | 15  | V    |
| V <sub>CC</sub> - | Supply Voltage                 |         | -5  | -15 | V    |
| т                 | Operating free air temperature | RC4558  | 0   | 70  | °C   |
| T <sub>A</sub>    | Operating free-air temperature | RC4558I | -40 | 85  | C    |

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## **5.4 Thermal Information**

|                      |  |             |                | RC4558      |             |               |      |
|----------------------|--|-------------|----------------|-------------|-------------|---------------|------|
|                      | THERMAL METRIC(1)                            | D<br>(SOIC) | DGK<br>(VSSOP) | P<br>(PDIP) | PS<br>(SOP) | PW<br>(TSSOP) | Unit |
|                      |  | 8 PINS      | 8 PINS         | 8 PINS      | 8 PINS      | 8 PINS        |      |
| $R_{\theta JA}$      | Junction-to-ambient thermal resistance       | 120.2       | 164.8          | 106         | 122.9       | 173.1         | °C/W |
| $R_{\theta JC(top)}$ | Junction-to-case (top) thermal resistance    | 59.6        | 58.8           | 84.9        | 60.1        | 81.8          | °C/W |
| $R_{\theta JB}$      | Junction-to-board thermal resistance         | 67.7        | 99.5           | 68.6        | 77.5        | 112.5         | °C/W |
| ΨЈТ                  | Junction-to-top characterization parameter   | 11.0        | 3.7            | 51.6        | 15.7        | 16.5          | °C/W |
| ΨЈВ                  | Junction-to-board characterization parameter | 66.7        | 97.7           | 67.8        | 76.0        | 110.7         | °C/W |
| $R_{\theta JC(bot)}$ | Junction-to-case (bottom) thermal resistance | N/A         | N/A            | N/A         | N/A         | N/A           | °C/W |

<sup>(1)</sup> For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application note.



## **5.5 Electrical Characteristics**

For V<sub>CC+</sub> = 15 V, V<sub>CC-</sub> = -15 V at T<sub>A</sub>  $\cong$  25°C, R<sub>L</sub> = 2 k $\Omega$  unless otherwise noted.

|                                  | PARAMETER  | TEST CONDITIONS <sup>(1)</sup>                      | TA  | MIN        | TYP    | MAX                    | UNIT               |  |
|----------------------------------|--|---|---|------------|--------|------------------------|--------------------|--|
| .,                               |  | V 9V  |   |            | 0.3    | 6                      | ٠,,                |  |
| Vos                              | Input offset voltage                                       | V <sub>O</sub> = 0V                                 | Full range <sup>(2)</sup>                     |            |        | 7.5                    | mV                 |  |
|                                  | land offer the comment                                     | V = 0V  |   |            | 5      | 200                    | A                  |  |
| I <sub>IO</sub>                  | Input offset current                                       | V <sub>O</sub> = 0V                                 | Full range <sup>(2)</sup>                     |            |        | 300                    | nA                 |  |
|                                  | Input high surrent   | V = 0V  |   | ,          | 80     | 500                    | Λ                  |  |
| I <sub>IB</sub>                  | Input bias current   | V <sub>O</sub> = 0V                                 | Full range <sup>(2)</sup>                     |            |        | 800                    | nA                 |  |
| V <sub>ICR</sub>                 | Common-mode input voltage range                            |   | ·   | ±12        | ±14    |                        | V                  |  |
|                                  |  | $R_L = 10k\Omega$                                   |   | ±12        | ±14.1  |                        |                    |  |
| $V_{OUT}$                        | Maximum output voltage swing                               | $R_L = 2k\Omega$                                    |   | ±10        | ±13.8  |                        | V                  |  |
|                                  |  | IV - 2K22   | Full range <sup>(2)</sup>                     | ±10        |        |                        |                    |  |
|                                  |  |   |   | 20         | 830    |                        | V/mV               |  |
| ۸                                | Large-signal differential voltage                          | $R_L \ge 2k\Omega$ ,                                |   | 86         | 118    |                        | dB                 |  |
| $A_{VD}$                         | amplification  | $V_O = \pm 10V$                                     | Full range <sup>(2)</sup>                     | 15         |        |                        | V/mV               |  |
|                                  |  |   | I ull range                                   | 83         |        |                        | dB                 |  |
| GBW                              | Gain-bandwidth product                                     | f = 10kHz   | ·   |            | 4      |                        | MHz                |  |
| SSBW                             | Small-signal bandwidth                                     | V <sub>O</sub> = 200mV <sub>PP</sub> , <1dB peaking |   |            | 3      |                        | MHz                |  |
| CMRR                             | Common-mode rejection ratio                                | (V-) + 3V < V <sub>ICR</sub> < (V+) - 3V            |   | 70         | 94     |                        | dB                 |  |
|                                  | Input impedance  | Common-mode   |   | 550    5.6 |        | MΩ    pF               |                    |  |
|                                  | input impedance  | Differential  |   | 450    0.8 |        | $k\Omega \parallel pF$ |                    |  |
| k <sub>SVS</sub>                 | Supply-voltage sensitivity $(\Delta V_{IO}/\Delta V_{CC})$ | $V_{CC} = \pm 5V$ to $\pm 15V$                      |   |            | 25     | 150                    | μV/V               |  |
| NSVS                             | Supply-voltage sensitivity (AVIO/AVCC)                     | ACC - TOA 10 T 10A                                  |   | 76         | 92     |                        | dB                 |  |
|                                  | Input voltage noise  | f = 0.1Hz to 10Hz                                   |   |            | 0.38   |                        | $\mu V_{PP}$       |  |
| ۵.,                              | input voltage noise  | 1 - 0.1112 to 10112                                 |   | 0.063      |        | $\mu V_{RMS}$          |                    |  |
| e <sub>N</sub>                   | Input voltage noise density                                | f = 1kHz  |   |            | 7      |                        | nV/√ <del>Hz</del> |  |
|                                  | input voltage noise density                                | f = 10kHz   |   |            | 6.5    |                        | 11V/NHZ            |  |
| I <sub>N</sub>                   | Input current noise density                                | f = 1kHz  |   |            | 0.15   |                        | pA/√Hz             |  |
| THD+N                            | Total harmonic distortion + noise                          | $V_{CC} = 30V, A_{VD} = 1V/V, f = 1kHz, V$          | $_{O}$ = 3V <sub>RMS</sub> , R <sub>L</sub> = |            | 0.0001 |                        | %                  |  |
| 1110.11                          | Total Harmonic distortion : Hoise                          | 2kΩ   |   |            | 120    |                        | dB                 |  |
| Icc                              | Supply current (both amplifiers)                           | V <sub>O</sub> = 0V, No load                        |   |            | 2.5    | 5.6                    | mA                 |  |
| 100                              | Supply current (both ampliners)                            | Vo = 0V, No load                                    | Full range <sup>(2)</sup>                     |            | 2.65   | 6.6                    | ША                 |  |
| V <sub>O1</sub> /V <sub>O2</sub> | Crosstalk attenuation                                      | $R_S = 1k\Omega$ , $f = 10kHz$ , $A_{VD} = 1V/V$    |   | -          | 120    |                        | dB                 |  |
| t <sub>r</sub>                   | Rise time  | V <sub>I</sub> = 20mV, C <sub>L</sub> = 100pF       |   |            | 67     |                        | ns                 |  |
|                                  | Overshoot  | V <sub>I</sub> = 20mV, C <sub>L</sub> = 100pF       |   |            | 16.8   |                        | %                  |  |
| SR                               | Slew rate  | $V_{STEP}$ = 10V, $C_L$ = 100pF                     | 1.1   | 2.2        |        | V/µs                   |                    |  |

<sup>(1)</sup> All characteristics are measured under open-loop conditions with zero common-mode input voltage, unless otherwise specified.

<sup>(2)</sup> Full range is 0°C to 70°C for RC4558 and -40°C to 85°C for RC4558I.

## **5.6 Typical Characteristics**

at  $T_A \cong 25^{\circ}\text{C}$ ,  $V_{CC} = 30\text{V}$  (±15V),  $V_{CM} = V_{CC} / 2$ ,  $R_L = 2k\Omega$  connected to  $V_{CC} / 2$  (unless otherwise noted)

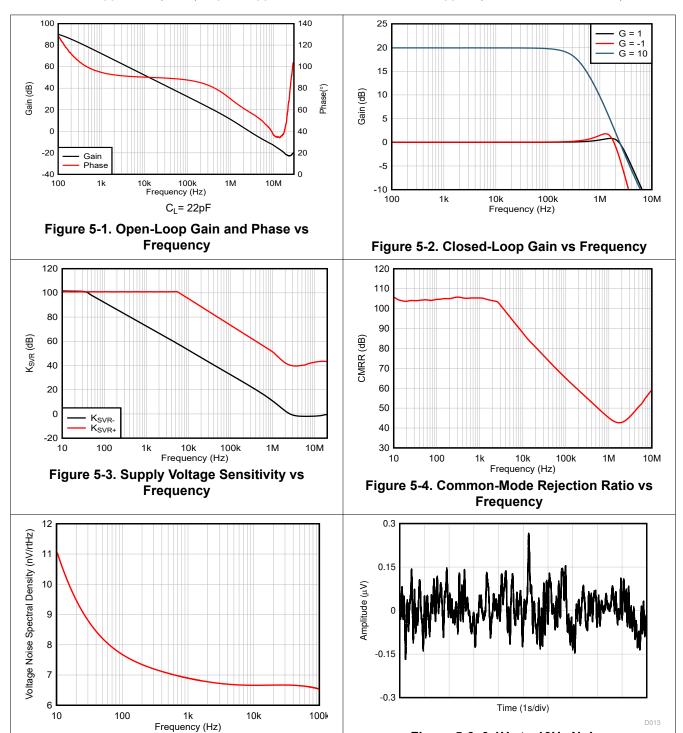
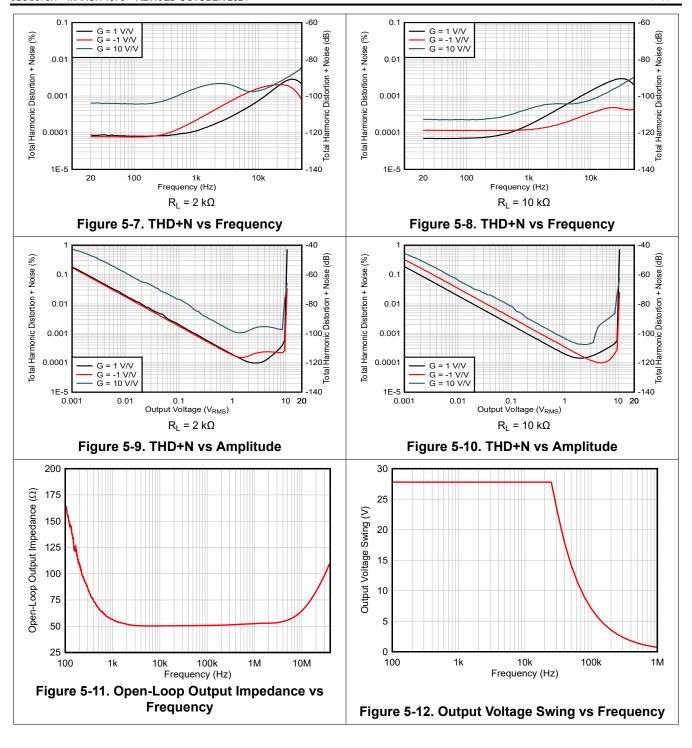
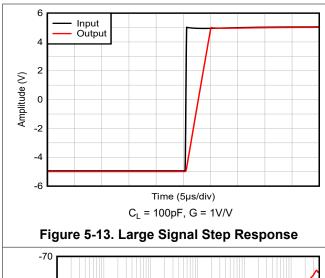


Figure 5-5. Input Noise Voltage vs Frequency

Figure 5-6. 0.1Hz to 10Hz Noise







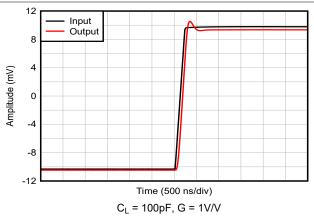
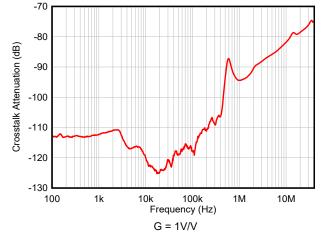


Figure 5-14. Small Signal Step Response



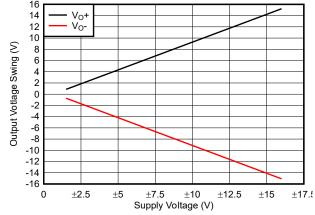
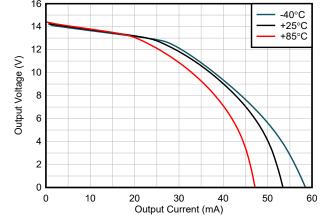


Figure 5-15. Crosstalk Attenuation vs Frequency

Figure 5-16. Maximum Output Voltage Swing vs
Operating Voltage



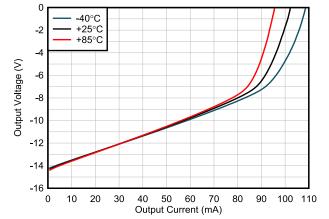
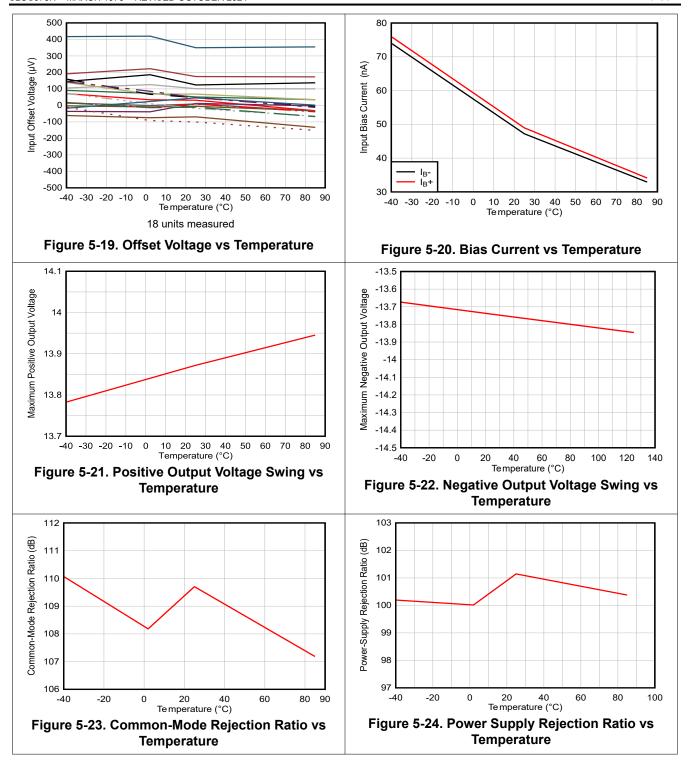
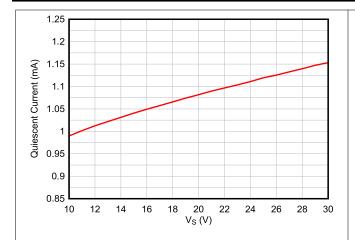


Figure 5-17. Output Voltage Swing vs Output Current (Sourcing)

Figure 5-18. Output Voltage Swing vs Output Current (Sinking)







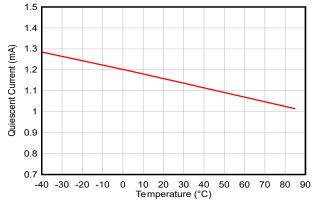
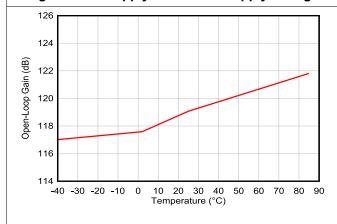


Figure 5-25. Supply Current vs Supply Voltage

Figure 5-26. Supply Current vs Temperature



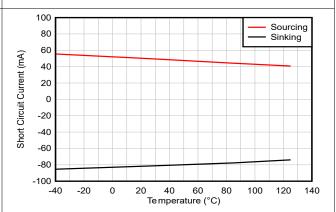


Figure 5-27. Open-Loop Gain vs Temperature

Figure 5-28. Short-Circuit Current vs Temperature



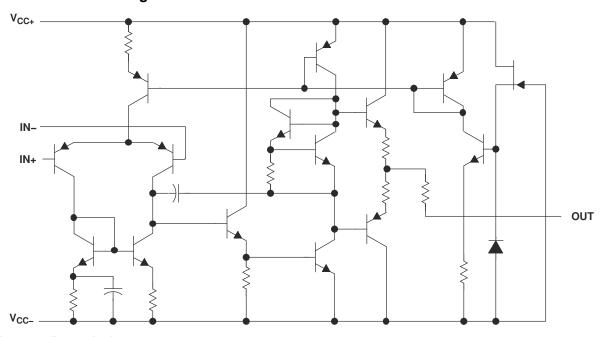
## **6 Detailed Description**

#### 6.1 Overview

The RC4558 device is a dual general-purpose operational amplifier. The combination of the wide supply voltage range (10V to 30V), low noise (6.5nV/ $\sqrt{\text{Hz}}$ ), and distortion performance (0.0001% THD+N) of the device allow the RC4558 to be used in various audio applications.

The high common-mode input voltage range and the absence of latch-up of this device are designed for voltage-follower applications. The internal frequency compensation of the device allows for stability without external components.

#### 6.2 Functional Block Diagram



#### 6.3 Feature Description

## 6.3.1 Unity-Gain Bandwidth

The unity-gain bandwidth is the frequency up to which an amplifier with a unity gain can be operated without greatly distorting the signal. The RC4558 device has a 4MHz gain-bandwidth product.

#### 6.3.2 Common-Mode Rejection Ratio

The common-mode rejection ratio (CMRR) of an amplifier is a measure of how well the device rejects unwanted input signals common to both input leads. The CMRR is found by taking the ratio of the change in input offset voltage to the change in the input voltage, then converting the ratio to decibels. Ideally the CMRR is infinite, but in practice, amplifiers are designed to have the CMRR as high as possible. The CMRR of the RC4558 device is 94dB.

#### 6.3.3 Slew Rate

The slew rate is the rate at which an operational amplifier can change the output when there is a change on the input. The RC4558 device has a 2.2V/µs slew rate.

#### **6.4 Device Functional Modes**

The RC4558 device is powered on when the supply is connected. Each of these devices can be operated as a single-supply operational amplifier or dual-supply amplifier depending on the application.

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# 7 Application and Implementation

#### Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

## 7.1 Application Information

The RC4558 is a dual general-purpose device that offers a wide supply range and excellent AC performance. This device operates up to 30V supply rails and offers low noise  $(6.5\text{nV}/\sqrt{\text{Hz}})$  and distortion performance (0.0001% THD+N). These RC4558 features are designed for both audio and industrial applications.

#### 7.2 Typical Application

Some applications require differential signals. Figure 7-1 shows a simple circuit to convert a single-ended input of 2V to 10V into differential output of  $\pm 8V$  on a single 15V supply. The output range is intentionally limited to maximize linearity. The circuit is composed of two amplifiers. One amplifier acts as a buffer and creates a voltage,  $V_{OUT+}$ . The second amplifier inverts the input and adds a reference voltage to generate  $V_{OUT-}$ . Both  $V_{OUT+}$  and  $V_{OUT-}$  range from 2V to 10V. The difference,  $V_{DIFF}$ , is the difference between  $V_{OUT+}$  and  $V_{OUT-}$ .

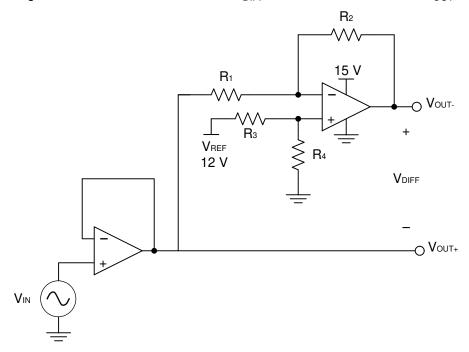


Figure 7-1. Schematic for Single-Ended Input to Differential Output Conversion

#### 7.2.1 Design Requirements

The design requirements are as follows:

Supply voltage: 15V
Reference voltage: 12V
Input: 2V to 10V
Output differential: ±8V

#### 7.2.2 Detailed Design Procedure

The circuit in Figure 7-1 takes a single-ended input signal,  $V_{IN}$ , and generates two output signals,  $V_{OUT+}$  and  $V_{OUT-}$ , using two amplifiers and a reference voltage,  $V_{REF}$ .  $V_{OUT+}$  is the output of the first amplifier and is a buffered version of the input signal,  $V_{IN}$  (see Equation 1).  $V_{OUT-}$  is the output of the second amplifier which uses  $V_{REF}$  to add an offset voltage to  $V_{IN}$  and feedback to add inverting gain. The transfer function for  $V_{OUT-}$  is Equation 2.

$$V_{OUT+} = V_{IN} \tag{1}$$

$$V_{OUT-} = V_{REF} \times \left(\frac{R_4}{R_3 + R_4}\right) \times \left(1 + \frac{R_2}{R_1}\right) - V_{IN} \times \frac{R_2}{R_1}$$
 (2)

The differential output signal,  $V_{DIFF}$ , is the difference between the two single-ended output signals,  $V_{OUT+}$  and  $V_{OUT-}$ . Equation 3 shows the transfer function for  $V_{DIFF}$ . By applying the conditions that  $R_1 = R_2$  and  $R_3 = R_4$ , the transfer function is simplified into Equation 6. Using this configuration, the maximum input signal is equal to the reference voltage and the maximum output of each amplifier is equal to the  $V_{REF}$ . The differential output range is  $2 \times V_{REF}$ . Furthermore, the common-mode voltage is one half of  $V_{REF}$  (see Equation 7).

$$V_{DIFF} = V_{OUT +} - V_{OUT -} = V_{IN} \times \left(1 + \frac{R_2}{R_1}\right) - V_{REF} \times \left(\frac{R_4}{R_3 + R_4}\right) \left(1 + \frac{R_2}{R_1}\right)$$
 (3)

$$V_{OIIT+} = V_{IN} \tag{4}$$

$$V_{OUT-} = V_{REF} - V_{IN}$$
 (5)

$$V_{DIFF} = 2 \times V_{IN} - V_{REF} \tag{6}$$

$$V_{CM} = \left(\frac{V_{OUT} + V_{OUT}}{2}\right) = \frac{1}{2}V_{REF} \tag{7}$$

#### 7.2.2.1 Amplifier Selection

Linearity over the input range is key for good DC accuracy. The common-mode input range and the output swing limitations determine the linearity. In general, an amplifier with rail-to-rail input and output swing is required. Bandwidth is a key concern for this design. The RC4558 device has a bandwidth of 4MHz, therefore this circuit can only process signals with frequencies of less than 4MHz.

#### 7.2.2.2 Passive Component Selection

The transfer function of  $V_{OUT-}$  is heavily reliant on resistors ( $R_1$ ,  $R_2$ ,  $R_3$ , and  $R_4$ ), therefore TI recommends to use resistors with low tolerances to maximize performance and minimize error. This design uses resistors with resistance values of

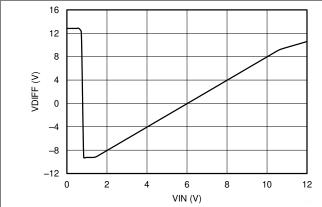
 $36k\Omega$  with tolerances measured to be within 2% of these resistor values. If the noise of the system is a key parameter, the user can select smaller resistance values ( $6k\Omega$  or lower) to keep the overall system noise low and the noise from the resistors lower than the amplifier noise.

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## 7.2.3 Application Curves

The measured transfer functions in Figure 7-2, Figure 7-3, and Figure 7-4 were generated by sweeping the input voltage from 0V to 12V. However, this design must only be used between 2V and 10V for optimum linearity.



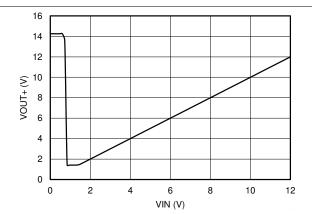


Figure 7-2. Differential Output Voltage Node vs Input Voltage

Figure 7-3. Positive Output Voltage Node vs Input Voltage

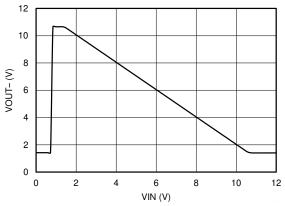


Figure 7-4. Positive Output Voltage Node vs Input Voltage

#### 7.3 Power Supply Recommendations

The RC4558 device is specified for ±5V to ±15V operation; many specifications apply for –0°C to 70°C. The *Typical Characteristics* section presents parameters that can exhibit significant variance with regard to operating voltage or temperature.

#### **CAUTION**

Supply voltages outside of the ±18V range can permanently damage the device (see the *Absolute Maximum Ratings*).

Place 0.1µF bypass capacitors close to the power-supply pins to reduce errors coupling in from noisy or high impedance power supplies. For more detailed information on bypass capacitor placement, refer to the *Layout Guidelines*.

#### 7.4 Layout

#### 7.4.1 Layout Guidelines

For best operational performance of the device, use good printed circuit board (PCB) layout practices, including:

- Noise can propagate into analog circuitry through the operational amplifier and the power pins of the circuit
  as a whole. Bypass capacitors are used to reduce the coupled noise by providing low impedance power
  sources local to the analog circuitry.
  - Connect low-ESR, 0.1µF ceramic bypass capacitors between each supply pin and ground, placed as close to the device as possible. A single bypass capacitor from V+ to ground is applicable for singlesupply applications.
- Separating grounding for analog and digital portions of circuitry is one of the simplest and most effective
  methods of noise suppression. One or more layers on multilayer PCBs are usually devoted to ground planes.
  A ground plane helps distribute heat and reduces EMI noise pickup. Make sure to physically separate digital
  and analog grounds, paying attention to the flow of the ground current.
- To reduce parasitic coupling, run the input traces as far away from the supply or output traces as possible. If
  it is not possible to keep the traces separate, it is much better to cross the sensitive trace perpendicular as
  opposed to in parallel with the noisy trace.
- Place the external components as close to the device as possible. Keeping RF and RG close to the inverting input minimizes parasitic capacitance, as shown in *Layout Example*.
- Keep the length of input traces as short as possible. Always remember that the input traces are the most sensitive part of the circuit.
- Consider a driven, low-impedance guard ring around the critical traces. A guard ring can significantly reduce leakage currents from nearby traces that are at different potentials.

#### 7.4.2 Layout Example

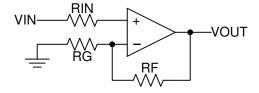


Figure 7-5. Operational Amplifier Schematic for Noninverting Configuration

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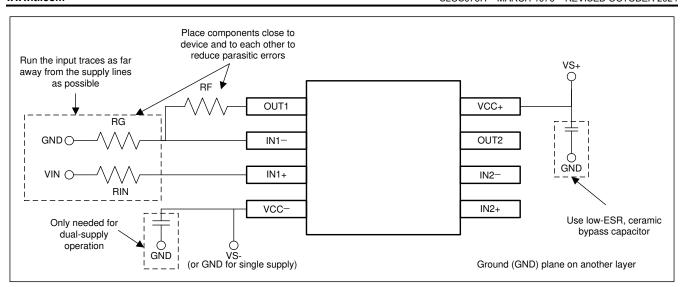


Figure 7-6. Operational Amplifier Board Layout for Noninverting Configuration



# **8 Device and Documentation Support**

#### 8.1 Trademarks

All trademarks are the property of their respective owners.

## 8.2 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

## 8.3 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms and definitions.

# **9 Revision History**

| C | hanges from Revision G (November 2014) to Revision H (October 2024)   | Page                                    |
|---|---|---|
| • | Updated Features, Applications, Description, Detailed Description, Feature Description, Detailed Design                           | <br>7                                   |
|   | Procedure, and Layout Guidelines sections to reflect the changes listed in the Specifications section                             | 1                                       |
| • | Changed Device Information table to Package Information   | 1                                       |
| • | Removed Duration of output short circuit to ground specification and added maximum output current of                              |   |
|   | ±125mA in Absolute Maximum Ratings table  | 4                                       |
| • | Updated Handling Ratings table to ESD Ratings table   | 4                                       |
| • | Updated Thermal Information table   | <mark>5</mark>                          |
| • | Changed the typical input offset voltage value from: 0.5mV to 0.3mV in the Electrical Characteristics tab                         | ole6                                    |
| • | Changed the typical Input bias current value from: 150nA to 80nA in the Electrical Characteristics table.                         | 6                                       |
| • | Changed the typical maximum output voltage swing value at $R_L = 10k\Omega$ from ±14V to ±14.1V in the Elec                       | ctrical                                 |
|   | Characteristics table   | 6                                       |
| • | Changed the typical maximum output voltage swing value at $R_L = 2k\Omega$ from: ±13V to ±13.8V in the Elec                       | trical                                  |
|   | Characteristics table   | 6                                       |
| • | Changed the typical large-signal differential voltage amplification value from: 300V/mV to 830V/mV in                             |   |
|   | the Electrical Characteristics table  | 6                                       |
| • | Added line items for the large-signal voltage amplification parameter to show values in dB units in                               |   |
|   | the Electrical Characteristics table  | 6                                       |
| • | Changed unity gain-bandwidth parameter to gain-bandwidth product and changed the typical value from                               | 1:                                      |
|   | 3MHz to 4MHz in the Electrical Characteristics table  | • |
| • | Added the small-signal bandwidth parameter in the Electrical Characteristics table  |   |
| • | Added test condition to the common-mode rejection ratio parameter in the Electrical Characteristics table                         |   |
| • | Changed the typical common-mode rejection ratio value from: 90dB to 94dB in the Electrical Characterist                           | stics                                   |
|   | table   | 6                                       |
| • | Removed the minimum limit for the <i>input resistance</i> parameter in the <i>Electrical Characteristics</i> table                | 6                                       |
| • | Updated the <i>input resistance</i> parameter to <i>input impedance</i> to better reflect device characteristics in               |   |
|   | the Electrical Characteristics table  | 6                                       |
| • | Changed the test condition of the supply-voltage sensitivity parameter from: $V_{CC} = \pm 15V$ to $\pm 9V$ to $V_{CC} = \pm 15V$ | = ±5V                                   |
|   | to ±15V in the Electrical Characteristics table   | 6                                       |
| • | Updated the typical <i>supply-voltage sensitivity</i> value from: 30μV/V to 25μV/V in   |   |
|   | the Electrical Characteristics table  | 6                                       |
| • | Added line items for supply-voltage sensitivity parameter to show values in dB units in the Electrical                            |   |
|   | Characteristics table   | 6                                       |
| • | Added input voltage noise parameter to the Electrical Characteristics table   | 6                                       |

Product Folder Links: RC4558

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| the Electrical Characteristics table.  Changed typical equivalent input noise voltage (closed loop) at f = 1 kHz from 8 nV/√Hz to 7 nV/√Hz in the Electrical Characteristics table.  Changed equivalent input noise voltage (closed loop) specification to input voltage noise density in the Electrical Characteristics table.  Added f = 10 kHz test condition to equivalent input noise voltage (closed loop) specification in the Electrical Characteristics table.  Added the input current noise density parameter to the Electrical Characteristics table.  Changed T <sub>A</sub> min and T <sub>A</sub> max conditions for supply current to one full range temperature condition in the Electrical Characteristics table.  Changed T <sub>A</sub> min and T <sub>A</sub> max conditions for supply current to one full range temperature condition in the Electrical Characteristics table.  Changed the typical supply current (both amplifiers) value at full temperature range from: 3 mA to 2.65 mA in the Electrical Characteristics table.  Changed the test condition for the crosstalk attenuation parameter from Open loop & A <sub>VD</sub> = 100 V/V to A <sub>VD</sub> = 1VV in the Electrical Characteristics table.  Changed the typical crosstalk attenuation value from: 105dB to 120 dB in the Electrical Characteristics table.  Changed the pipical crosstalk attenuation value from: 105dB to 120 dB in the Electrical Characteristics table.  Changed the vipical value from: 5% to 16.8% in the Electrical Characteristics table.  Changed the siew rate typical value from: 5% to 16.8% in the Electrical Characteristics table.  Changed the siew rate typical value from: 1.7V/µs to 2.2V/µs in the Electrical Characteristics table.  Changed and added graphs to the Typical Characteristics section.  Changes from Revision F (September 2010) to Revision G (November 2014)  Page  Added Applications, Device Information table, Handling Ratings table, Feature Description section, Device Functional Modes, Application and Implementation section, Power Supply Recommendations section, Layout section, Device and Documentation Support sect | •  | Changed test conditions of <i>equivalent input noise voltage (closed loop)</i> parameter to f = 1 kHz in  |     |
|---|----|---|-----|
| the Electrical Characteristics table  |    | the Electrical Characteristics table  | 6   |
| <ul> <li>Changed equivalent input noise voltage (closed loop) specification to input voltage noise density in the Electrical Characteristics table.</li> <li>Added f = 10 kHz test condition to equivalent input noise voltage (closed loop) specification in the Electrical Characteristics table.</li> <li>Added the input current noise density parameter to the Electrical Characteristics table.</li> <li>Removed the total power dissipation parameter in the Electrical Characteristics table.</li> <li>Changed T<sub>A</sub> min and T<sub>A</sub> max conditions for supply current to one full range temperature condition in the Electrical Characteristics table.</li> <li>Changed the typical supply current (both amplifiers) value at full temperature range from: 3 mA to 2.65 mA in the Electrical Characteristics table.</li> <li>Changed the test condition for the crosstalk attenuation parameter from Open loop &amp; A<sub>VD</sub> = 100 V/V to A<sub>VD</sub> = 1V/V in the Electrical Characteristics table.</li> <li>Changed the typical crosstalk attenuation value from: 105dB to 120 dB in the Electrical Characteristics table.</li> <li>Changed the rise time typical value from: 0.13 ns to 67 ns in the Electrical Characteristics table.</li> <li>Changed the overshoot typical value from: 5% to 16.8% in the Electrical Characteristics table.</li> <li>Changed the siew rate typical value from: 1.7V/µs to 2.2V/µs in the Electrical Characteristics table.</li> <li>Changed and added graphs to the Typical Characteristics section.</li> <li>Added Applications, Device Information table, Handling Ratings table, Feature Description section, Device Functional Modes, Application and Implementation section, Power Supply Recommendations section, Layout section, Device and Documentation Support section, and Mechanical, Packaging, and Orderable Information section.</li> </ul>  | •  | Changed typical equivalent input noise voltage (closed loop) at f = 1 kHz from 8 nV/ $\sqrt{Hz}$ to 7 nV/ $\sqrt{Hz}$ in  |     |
| the Electrical Characteristics table  |    | the Electrical Characteristics table  | 6   |
| <ul> <li>Added f = 10 kHz test condition to equivalent input noise voltage (closed loop) specification in the Electrical Characteristics table</li></ul>  | •  | Changed equivalent input noise voltage (closed loop) specification to input voltage noise density in  |     |
| <ul> <li>Characteristics table</li></ul>  |    | the Electrical Characteristics table  | 6   |
| <ul> <li>Added the <i>input current noise density</i> parameter to the <i>Electrical Characteristics</i> table</li></ul>  | •  | Added <i>f</i> = 10 kHz test condition to <i>equivalent input noise voltage</i> (closed loop) specification in the <i>Electrical</i>  |     |
| <ul> <li>Removed the <i>total power dissipation</i> parameter in the <i>Electrical Characteristics</i> table</li></ul>  |    | Characteristics table   | . 6 |
| <ul> <li>Changed T<sub>A</sub> min and T<sub>A</sub> max conditions for supply current to one full range temperature condition in the Electrical Characteristics table</li></ul>  | •  | Added the input current noise density parameter to the Electrical Characteristics table   | .6  |
| the Electrical Characteristics table  | •  | Removed the total power dissipation parameter in the Electrical Characteristics table   | . 6 |
| <ul> <li>Changed the typical supply current (both amplifiers) value at full temperature range from: 3 mA to 2.65 mA in the Electrical Characteristics table</li></ul>   | •  | Changed $T_A$ min and $T_A$ max conditions for supply current to one full range temperature condition in  |     |
| the Electrical Characteristics table  |    | the Electrical Characteristics table  | 6   |
| <ul> <li>Changed the test condition for the <i>crosstalk attenuation</i> parameter from <i>Open loop</i> &amp; A<sub>VD</sub> = 100 V/V to A<sub>VD</sub> = 1V/V in the <i>Electrical Characteristics</i> table</li></ul>   | •  | Changed the typical supply current (both amplifiers) value at full temperature range from: 3 mA to 2.65 mA in   | n   |
| <ul> <li>1V/V in the Electrical Characteristics table</li></ul>   |    |   | _   |
| <ul> <li>Changed the typical crosstalk attenuation value from: 105dB to 120 dB in the Electrical Characteristics table.</li> <li>Changed the rise time typical value from: 0.13 ns to 67 ns in the Electrical Characteristics table.</li> <li>Changed the overshoot typical value from: 5% to 16.8% in the Electrical Characteristics table.</li> <li>Changed the slew rate typical value from: 1.7V/µs to 2.2V/µs in the Electrical Characteristics table.</li> <li>Changed and added graphs to the Typical Characteristics section.</li> <li>Total Characteristics table.</li> <li>Added Applications, Device Information table, Handling Ratings table, Feature Description section, Device Functional Modes, Application and Implementation section, Power Supply Recommendations section, Layout section, Device and Documentation Support section, and Mechanical, Packaging, and Orderable Information section.</li> </ul>   | •  | Changed the test condition for the <i>crosstalk attenuation</i> parameter from <i>Open loop</i> & $A_{VD}$ = 100 V/V to $A_{VD}$ :  | =   |
| <ul> <li>Changed the rise time typical value from: 0.13 ns to 67 ns in the Electrical Characteristics table</li></ul>   |    | 1V/V in the Electrical Characteristics table  | .6  |
| <ul> <li>Changed the overshoot typical value from: 5% to 16.8% in the Electrical Characteristics table</li></ul>  | •  | Changed the typical crosstalk attenuation value from: 105dB to 120 dB in the Electrical Characteristics table   | 6   |
| <ul> <li>Changed the slew rate typical value from: 1.7V/µs to 2.2V/µs in the Electrical Characteristics table</li></ul>   | •  | Changed the <i>rise time</i> typical value from: 0.13 ns to 67 ns in the <i>Electrical Characteristics</i> table  | .6  |
| <ul> <li>Changed and added graphs to the Typical Characteristics section</li></ul>  | •  | Changed the overshoot typical value from: 5% to 16.8% in the Electrical Characteristics table   | .6  |
| Changes from Revision F (September 2010) to Revision G (November 2014)  • Added Applications, Device Information table, Handling Ratings table, Feature Description section, Device Functional Modes, Application and Implementation section, Power Supply Recommendations section, Layout section, Device and Documentation Support section, and Mechanical, Packaging, and Orderable Information section.   | •  | Changed the slew rate typical value from: 1.7V/µs to 2.2V/µs in the Electrical Characteristics table  | . 6 |
| <ul> <li>Added Applications, Device Information table, Handling Ratings table, Feature Description section, Device Functional Modes, Application and Implementation section, Power Supply Recommendations section, Layout section, Device and Documentation Support section, and Mechanical, Packaging, and Orderable Information section</li></ul>   | •  | Changed and added graphs to the <i>Typical Characteristics</i> section  | .7  |
| <ul> <li>Added Applications, Device Information table, Handling Ratings table, Feature Description section, Device Functional Modes, Application and Implementation section, Power Supply Recommendations section, Layout section, Device and Documentation Support section, and Mechanical, Packaging, and Orderable Information section</li></ul>   |    |   | _   |
| Functional Modes, Application and Implementation section, Power Supply Recommendations section, Layout section, Device and Documentation Support section, and Mechanical, Packaging, and Orderable Information section  | CI | nanges from Revision F (September 2010) to Revision G (November 2014)  Pag  | jе  |
|   | •  | Functional Modes, Application and Implementation section, Power Supply Recommendations section, Layou section, Device and Documentation Support section, and Mechanical, Packaging, and Orderable Information |     |
|   | •  |   | . 1 |

# 10 Mechanical, Packaging, and Orderable Information

The following pages include mechanical packaging and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser based versions of this data sheet, refer to the left hand navigation.

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#### **PACKAGING INFORMATION**

| Orderable Device | Status   | Package Type | Package<br>Drawing | Pins | Package<br>Qty | Eco Plan     | Lead finish/<br>Ball material | MSL Peak Temp      | Op Temp (°C) | Device Marking<br>(4/5) | Samples |
|------------------|----------|--------------|--------------------|------|----------------|--------------|-------------------------------|--------------------|--------------|-------------------------|---------|
| RC4558D          | OBSOLETE | SOIC         | D                  | 8    |                | TBD          | Call TI                       | Call TI            | 0 to 70      | RC4558                  |         |
| RC4558DGKR       | ACTIVE   | VSSOP        | DGK                | 8    | 2500           | RoHS & Green | NIPDAU   NIPDAUAG             | Level-1-260C-UNLIM | 0 to 70      | (YRP, YRS, YRU)         | Samples |
| RC4558DGKRG4     | ACTIVE   | VSSOP        | DGK                | 8    | 2500           | TBD          | Call TI                       | Call TI            | 0 to 70      |                         | Samples |
| RC4558DR         | ACTIVE   | SOIC         | D                  | 8    | 2500           | RoHS & Green | NIPDAU   SN                   | Level-1-260C-UNLIM | 0 to 70      | RC4558                  | Samples |
| RC4558DRG3       | OBSOLETE | SOIC         | D                  | 8    |                | TBD          | Call TI                       | Call TI            | 0 to 70      | RC4558                  |         |
| RC4558DRG4       | OBSOLETE | SOIC         | D                  | 8    |                | TBD          | Call TI                       | Call TI            | 0 to 70      | RC4558                  |         |
| RC4558ID         | OBSOLETE | SOIC         | D                  | 8    |                | TBD          | Call TI                       | Call TI            | -40 to 85    | R4558I                  |         |
| RC4558IDGKR      | ACTIVE   | VSSOP        | DGK                | 8    | 2500           | RoHS & Green | NIPDAU                        | Level-1-260C-UNLIM | -40 to 85    | (YSP, YSS, YSU)         | Samples |
| RC4558IDR        | ACTIVE   | SOIC         | D                  | 8    | 2500           | RoHS & Green | NIPDAU                        | Level-1-260C-UNLIM | -40 to 85    | R4558I                  | Samples |
| RC4558IP         | ACTIVE   | PDIP         | Р                  | 8    | 50             | RoHS & Green | NIPDAU                        | N / A for Pkg Type | -40 to 85    | RC4558IP                | Samples |
| RC4558IPW        | OBSOLETE | TSSOP        | PW                 | 8    |                | TBD          | Call TI                       | Call TI            | -40 to 85    | R4558I                  |         |
| RC4558IPWR       | ACTIVE   | TSSOP        | PW                 | 8    | 2000           | RoHS & Green | NIPDAU                        | Level-1-260C-UNLIM | -40 to 85    | R4558I                  | Samples |
| RC4558P          | ACTIVE   | PDIP         | Р                  | 8    | 50             | RoHS & Green | NIPDAU                        | N / A for Pkg Type | 0 to 70      | RC4558P                 | Samples |
| RC4558PSR        | ACTIVE   | SO           | PS                 | 8    | 2000           | RoHS & Green | NIPDAU                        | Level-1-260C-UNLIM | 0 to 70      | R4558                   | Samples |
| RC4558PSRG4      | ACTIVE   | SO           | PS                 | 8    | 2000           | RoHS & Green | NIPDAU                        | Level-1-260C-UNLIM | 0 to 70      | R4558                   | Samples |
| RC4558PW         | OBSOLETE | TSSOP        | PW                 | 8    |                | TBD          | Call TI                       | Call TI            | 0 to 70      | R4558                   |         |
| RC4558PWR        | ACTIVE   | TSSOP        | PW                 | 8    | 2000           | RoHS & Green | NIPDAU                        | Level-1-260C-UNLIM | 0 to 70      | R4558                   | Samples |

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.



## PACKAGE OPTION ADDENDUM

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(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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## TAPE AND REEL INFORMATION



# TAPE DIMENSIONS + K0 - P1 - B0 W Cavity - A0 -

| A0 | Dimension designed to accommodate the component width     |
|----|---|
| В0 | Dimension designed to accommodate the component length    |
| K0 | Dimension designed to accommodate the component thickness |
| W  | Overall width of the carrier tape                         |
| P1 | Pitch between successive cavity centers                   |

#### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

| Device      | Package<br>Type | Package<br>Drawing |   | SPQ  | Reel<br>Diameter<br>(mm) | Reel<br>Width<br>W1 (mm) | A0<br>(mm) | B0<br>(mm) | K0<br>(mm) | P1<br>(mm) | W<br>(mm) | Pin1<br>Quadrant |
|-------------|-----------------|--------------------|---|------|--------------------------|--------------------------|------------|------------|------------|------------|-----------|------------------|
| RC4558DGKR  | VSSOP           | DGK                | 8 | 2500 | 330.0                    | 12.4                     | 6.4        | 5.2        | 2.1        | 8.0        | 12.0      | Q1               |
| RC4558DR    | SOIC            | D                  | 8 | 2500 | 330.0                    | 12.4                     | 6.4        | 5.2        | 2.1        | 8.0        | 12.0      | Q1               |
| RC4558DR    | SOIC            | D                  | 8 | 2500 | 330.0                    | 12.4                     | 6.4        | 5.2        | 2.1        | 8.0        | 12.0      | Q1               |
| RC4558DR    | SOIC            | D                  | 8 | 2500 | 330.0                    | 12.4                     | 6.4        | 5.2        | 2.1        | 8.0        | 12.0      | Q1               |
| RC4558IDGKR | VSSOP           | DGK                | 8 | 2500 | 330.0                    | 12.4                     | 6.4        | 5.2        | 2.1        | 8.0        | 12.0      | Q1               |
| RC4558IDR   | SOIC            | D                  | 8 | 2500 | 330.0                    | 12.4                     | 6.4        | 5.2        | 2.1        | 8.0        | 12.0      | Q1               |
| RC4558IDR   | SOIC            | D                  | 8 | 2500 | 330.0                    | 12.4                     | 6.4        | 5.2        | 2.1        | 8.0        | 12.0      | Q1               |
| RC4558IPWR  | TSSOP           | PW                 | 8 | 2000 | 330.0                    | 12.4                     | 7.0        | 3.6        | 1.6        | 8.0        | 12.0      | Q1               |
| RC4558IPWR  | TSSOP           | PW                 | 8 | 2000 | 330.0                    | 12.4                     | 7.0        | 3.6        | 1.6        | 8.0        | 12.0      | Q1               |
| RC4558PSR   | so              | PS                 | 8 | 2000 | 330.0                    | 16.4                     | 8.35       | 6.6        | 2.4        | 12.0       | 16.0      | Q1               |
| RC4558PWR   | TSSOP           | PW                 | 8 | 2000 | 330.0                    | 12.4                     | 7.0        | 3.6        | 1.6        | 8.0        | 12.0      | Q1               |
| RC4558PWR   | TSSOP           | PW                 | 8 | 2000 | 330.0                    | 12.4                     | 7.0        | 3.6        | 1.6        | 8.0        | 12.0      | Q1               |



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\*All dimensions are nominal

| Device      | Package Type | Package Drawing | Pins | SPQ  | Length (mm) | Width (mm) | Height (mm) |
|-------------|--------------|-----------------|------|------|-------------|------------|-------------|
| RC4558DGKR  | VSSOP        | DGK             | 8    | 2500 | 353.0       | 353.0      | 32.0        |
| RC4558DR    | SOIC         | D               | 8    | 2500 | 356.0       | 356.0      | 35.0        |
| RC4558DR    | SOIC         | D               | 8    | 2500 | 353.0       | 353.0      | 32.0        |
| RC4558DR    | SOIC         | D               | 8    | 2500 | 353.0       | 353.0      | 32.0        |
| RC4558IDGKR | VSSOP        | DGK             | 8    | 2500 | 353.0       | 353.0      | 32.0        |
| RC4558IDR   | SOIC         | D               | 8    | 2500 | 340.5       | 338.1      | 20.6        |
| RC4558IDR   | SOIC         | D               | 8    | 2500 | 353.0       | 353.0      | 32.0        |
| RC4558IPWR  | TSSOP        | PW              | 8    | 2000 | 353.0       | 353.0      | 32.0        |
| RC4558IPWR  | TSSOP        | PW              | 8    | 2000 | 356.0       | 356.0      | 35.0        |
| RC4558PSR   | SO           | PS              | 8    | 2000 | 356.0       | 356.0      | 35.0        |
| RC4558PWR   | TSSOP        | PW              | 8    | 2000 | 353.0       | 353.0      | 32.0        |
| RC4558PWR   | TSSOP        | PW              | 8    | 2000 | 356.0       | 356.0      | 35.0        |

# **PACKAGE MATERIALS INFORMATION**

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## **TUBE**



#### \*All dimensions are nominal

| Device   | Package Name | Package Type | Pins | SPQ | L (mm) | W (mm) | T (µm) | B (mm) |
|----------|--------------|--------------|------|-----|--------|--------|--------|--------|
| RC4558IP | Р            | PDIP         | 8    | 50  | 506    | 13.97  | 11230  | 4.32   |
| RC4558P  | Р            | PDIP         | 8    | 50  | 506    | 13.97  | 11230  | 4.32   |



SMALL OUTLINE INTEGRATED CIRCUIT



- 1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
- 4. This dimension does not include interlead flash.
- 5. Reference JEDEC registration MS-012, variation AA.



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE INTEGRATED CIRCUIT



#### NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.





NOTES: A. All linear dimensions are in millimeters.

B. This drawing is subject to change without notice.

C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15.



# PS (R-PDSO-G8)

# PLASTIC SMALL OUTLINE



- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



# P (R-PDIP-T8)

# PLASTIC DUAL-IN-LINE PACKAGE



- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. Falls within JEDEC MS-001 variation BA.







- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

  2. This drawing is subject to change without notice.

  3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153, variation AA.





NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.





NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.







PowerPAD is a trademark of Texas Instruments.

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

  2. This drawing is subject to change without notice.

  3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-187.





NOTES: (continued)

- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.
- 8. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.
- 9. Size of metal pad may vary due to creepage requirement.





NOTES: (continued)

- 11. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 12. Board assembly site may have different recommendations for stencil design.



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